

# BRCS080N04SC

Rev.A Jun.-2022

## 描述 / Descriptions

SOP-8 塑封封装 N 沟道场效应管。

N-Channel Enhancement Mode Field Effect Transistor in a SOP-8 Plastic Package.

## 特征 / Features

$V_{DS} = 40V$

$I_D = 15A (V_{GS} = \pm 20V)$

$R_{DS(ON)} @ 10V \leq 8mR (Typ. 6.4mR)$

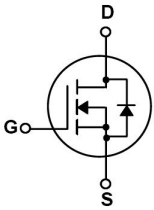
无卤产品。HF Product.

## 用途 / Applications

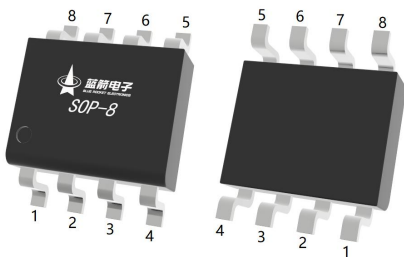
用于电源管理，便携式设备和电池供电系统。

Power Management in Notebook computer, Portable Equipment and Battery powered systems.

## 内部等效电路 / Equivalent Circuit



## 引脚排列 / Pinning



PIN 1 : S    PIN 2 : S    PIN 3 : S    PIN 4 : G  
PIN 5 : D    PIN 6 : D    PIN 7 : D    PIN 8 : D

## 印章代码 / Marking

见印章说明 See Marking Instructions.

**极限参数 / Absolute Maximum Ratings(Ta=25°C)**

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	$V_{DSS}$	40	V
Drain Current	$I_D(T_C=25^\circ\text{C})$	15	A
Drain Current - Pulsed	$I_{DM}$	68	A
Gate-Source Voltage	$V_{GSS}$	$\pm 20$	V
Single Pulsed Avalanche Energy	$E_{AS}$	67.6	mJ
Avalanche Current	$I_{AS}$	13	A
Power Dissipation	$P_D(T_C=25^\circ\text{C})$	3.1	W
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Junction-to-Ambient	$t \leq 10$	40	$^\circ\text{C/W}$
Junction-to-Ambient	Steady-State		
Junction-to-Lead	Steady-State	24	

## 电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions		最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$	$I_D=250\mu A$	40	47		V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=40V$	$V_{GS}=0V$			1	$\mu A$
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 20V$	$V_{DS}=0V$			$\pm 0.1$	$\mu A$
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$	$I_D=250\mu A$	1.0	1.6	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$	$I_D=20A$		6.4	8	$m\Omega$
		$V_{GS}=4.5V$	$I_D=10A$		10	13	$m\Omega$
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0V$	$I_S=1A$			1.2	V
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $f=1.0MHz$	$V_{GS}=0V$		850		pF
Output Capacitance	$C_{oss}$				115		
Reverse Transfer Capacitance	$C_{rss}$				30		
Gate resistance	$R_g$	$V_{GS}=0V$ $f=1MHz$	$V_{DS}=0V$		1.9		$\Omega$
Total Gate Charge	$Q_{g(10V)}$	$V_{GS}=10V$ $I_D=15A$	$V_{DS}=20V$		21		nC
Total Gate Charge	$Q_{g(4.5V)}$				8.6		
Gate Source Charge	$Q_{gs}$				5.7		
Gate Drain Charge	$Q_{gd}$				3		
Turn-On Delay Time	$t_{d(on)}$	$V_{GS}=10V$ $R_L=1.18\Omega$	$V_{DS}=20V$ $R_{GEN}=3.0\Omega$		7.5		ns
Turn-On Rise Time	$t_r$				2.1		
Turn-Off Delay Time	$t_{d(off)}$				23		
Turn-Off Fall Time	$t_f$				3		

电参数曲线图 / Electrical Characteristic Curve

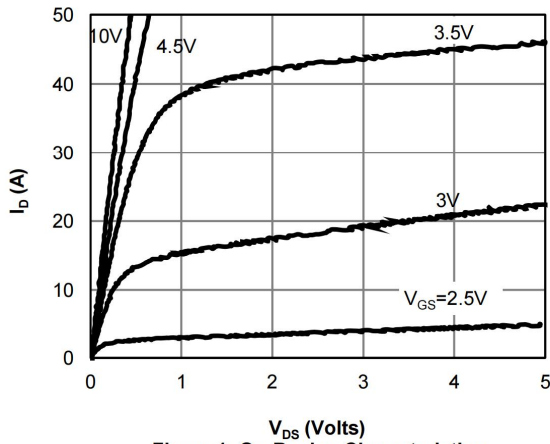


Figure 1: On-Region Characteristics

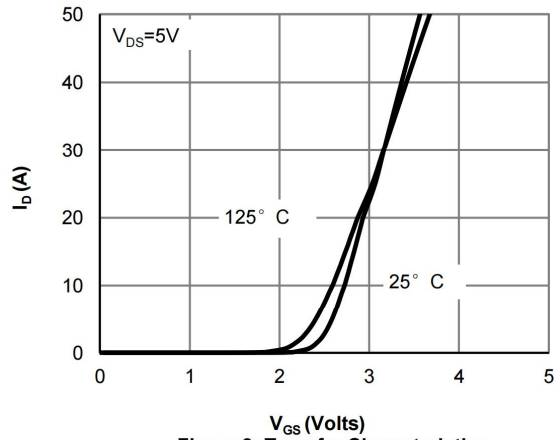


Figure 2: Transfer Characteristics

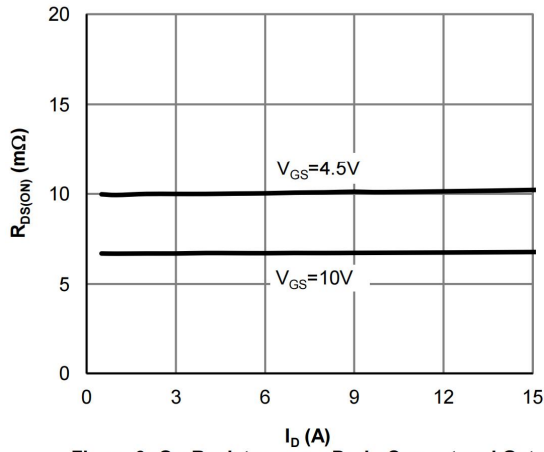


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

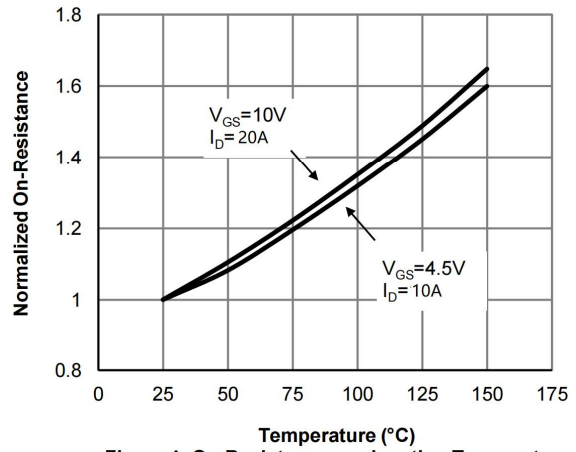


Figure 4: On-Resistance vs. Junction Temperature

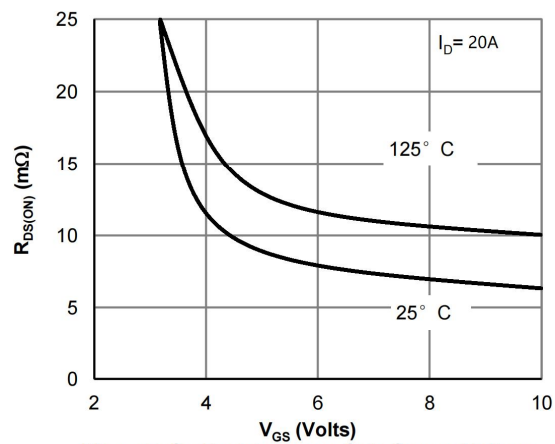


Figure 5: On-Resistance vs. Gate-Source Voltage

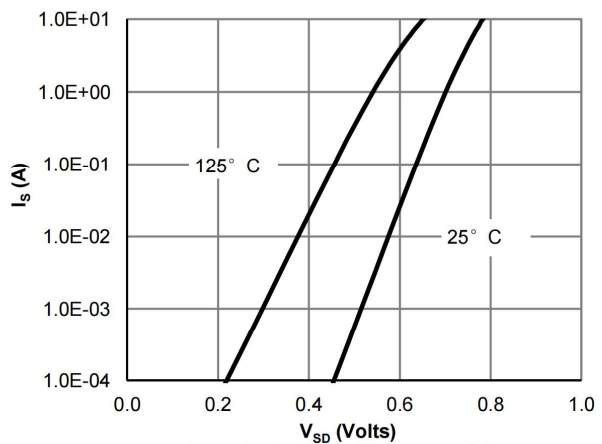


Figure 6: Body-Diode Characteristics

**电参数曲线图 / Electrical Characteristic Curve**

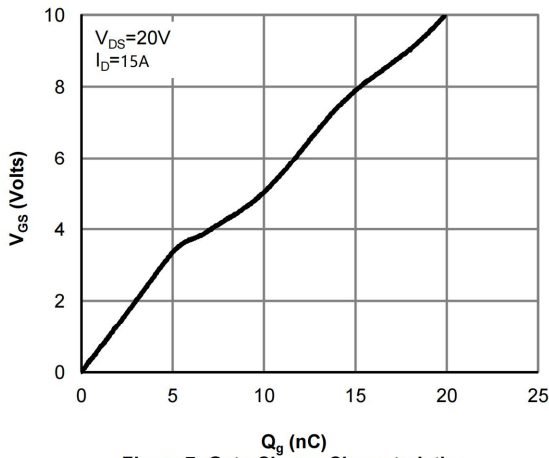


Figure 7: Gate-Charge Characteristics

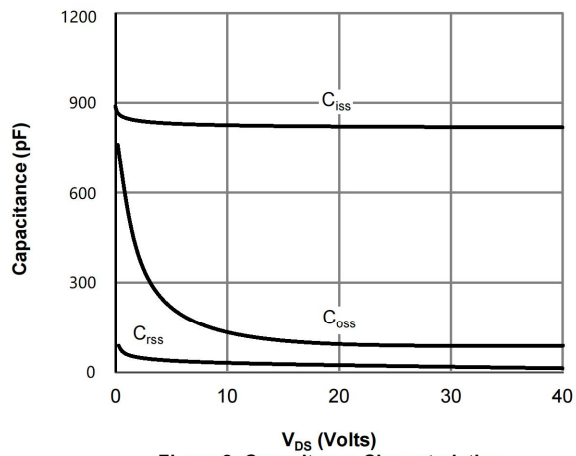


Figure 8: Capacitance Characteristics

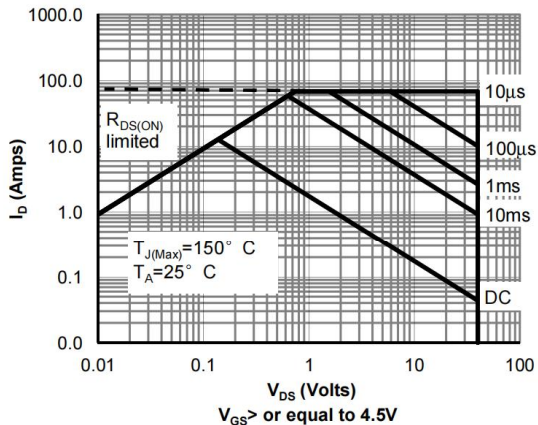


Figure 9: Maximum Forward Biased Safe Operating Area

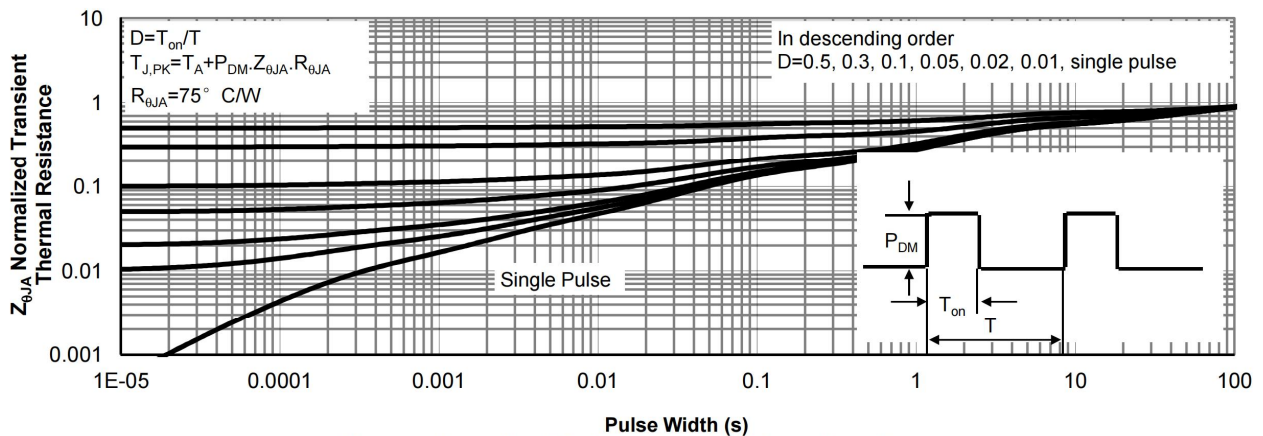
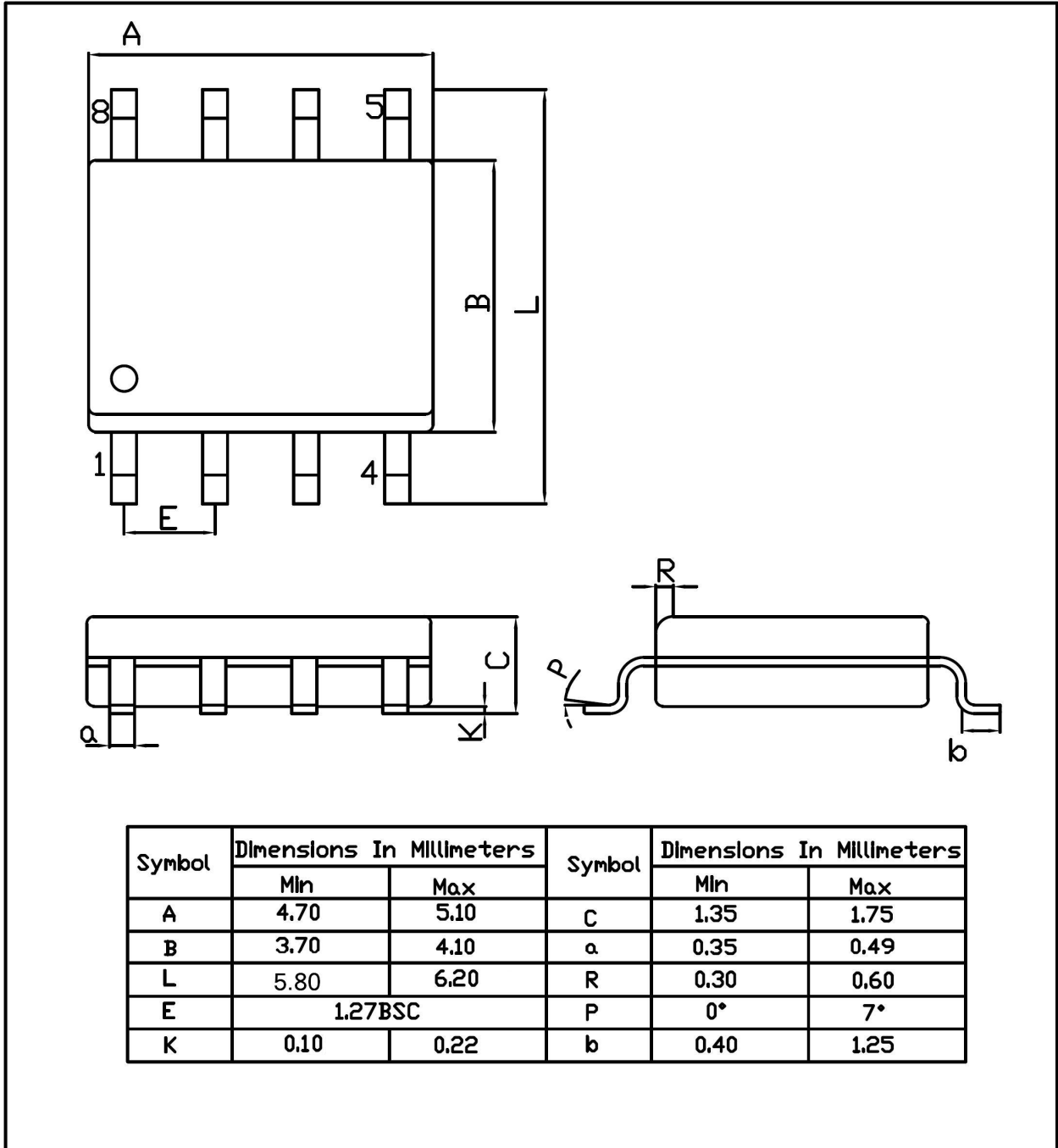


Figure 10: Normalized Maximum Transient Thermal Impedance

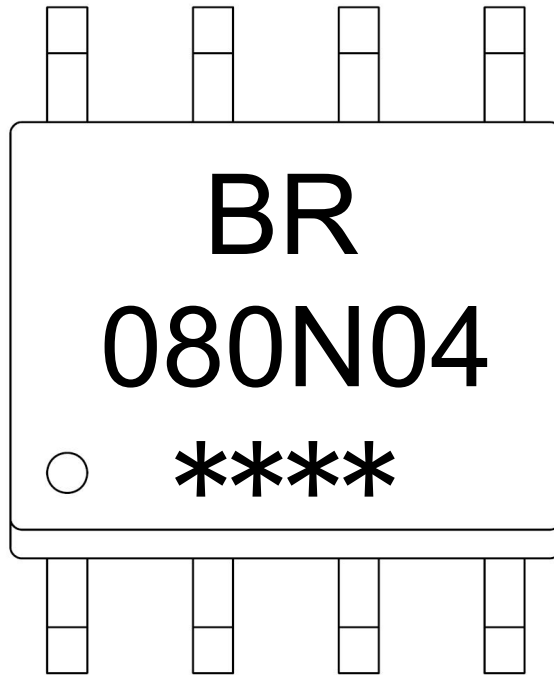
外形尺寸图 / Package Dimensions

SOP-8

Unit:mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

080N04： 为型号代码

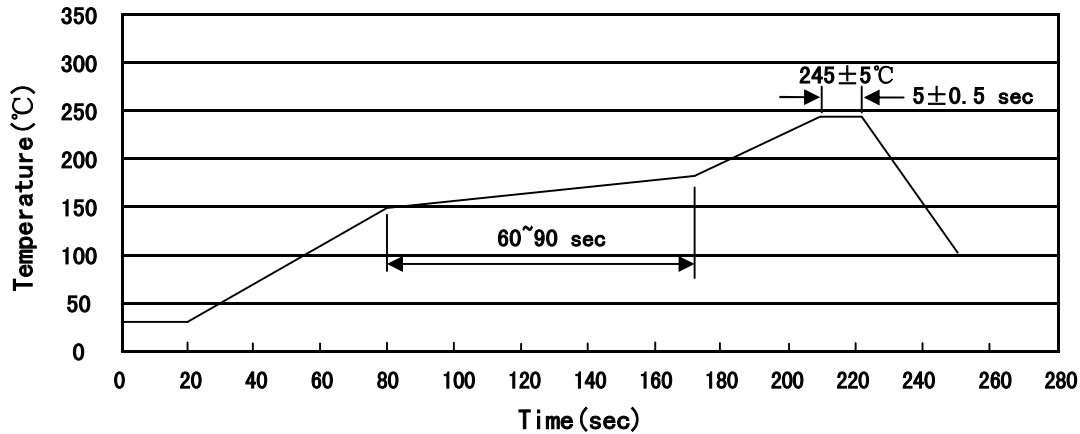
\*\*\*\*： 为生产批号代码，随生产批号变化

Note:

BR: Company Code

080N04: Product Type

\*\*\*\*: Lot No. Code, code change with Lot No

**回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)**


说明：

- 1、预热温度 150~180°C，时间 60~90sec;
- 2、峰值温度 245±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~180°C, Time:60~90sec.
- 2.Peak Temp.:245±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

**耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions**

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

**包装规格 / Packaging SPEC.**

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm <sup>3</sup> )		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOP/ESOP-8	4,000	2	8,000	6	48,000	13" ×12	360×360×50	380×335×366

**使用说明 / Notices**



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